



DMG9N65CT

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	Package	I _{D MAX} T _C = +25°C
650V	$1.3\Omega @ V_{GS} = 10V$	TO220AB	9.0A

Description

This new generation complementary dual MOSFET features low onresistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

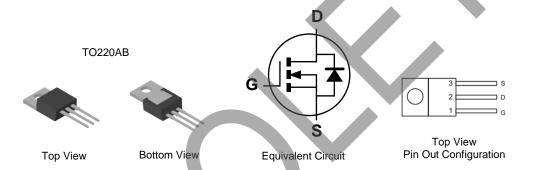
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)



Ordering Information (Note 4)

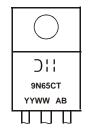
Ξ				
I	Part Number		Case	Packaging
I	DMG9N65CT		TO220AB	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

TO220AB



Oll = Manufacturer's Marking 9N65CT = Product Type Marking Code AB = Foundry and Assembly Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week (01 to 53)

DMG9N65CT Document number: DS35619 Rev. 10 - 4



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic				Value	Unit	
Drain-Source Voltage				650	V	
Gate-Source Voltage				±30	V	
Continuous Dusin Comment (Note 5) \	Steady	$T_{C} = +25^{\circ}C$		9.0	^	
Continuous Drain Current (Note 5) V _{GS} = 10V	State	$T_C = +70$ °C	ID	7.0	A	
Pulsed Drain Current (Note 6) 10µs Pulse, Pulse Duty Cycle<=1%			I _{DM}	30	Α	
Avalanche Current (Note 7) V _{DD} = 100V, V _{GS} = 10V, L = 60mH			I _{AR}	2.7	Α	
Repetitive Avalanche Energy (Note 7) V _{DD} = 100V, V _{GS} = 10V, L = 60mH				260	mJ	

Thermal Characteristics

Characteristic		Symbol	Max	Unit
	$T_C = +25^{\circ}C$		165	
Power Dissipation (Note 5)	T _C = +70°C	P _D	100	W
Thermal Resistance, Junction to 0	Case (Note 5)	Rejc	0.7	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

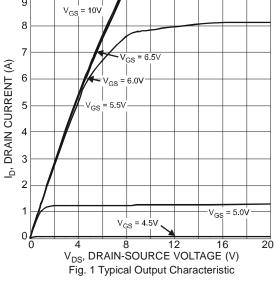
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

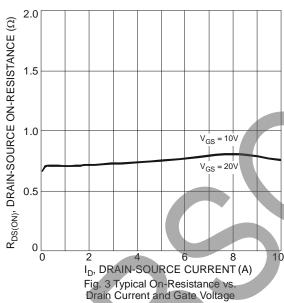
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		650	7	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}			1.0	μA	$V_{DS} = 650V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	_	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	3	_	5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		0.7	1.3	Ω	$V_{GS} = 10V, I_D = 4.5A$	
Forward Transfer Admittance	Y _{fs}	-	8.5		S	$V_{DS} = 40V, I_D = 4.5A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	2,310	l		N 051/ 1/ 01/	
Output Capacitance	Coss	_	122	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	2.2	_		I = I.OIVIHZ	
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{g}	_	39	_		V _{GS} = 10V, V _{DS} = 520V, I _D = 8A	
Gate-Source Charge	Q_{gs}	_	8.5	_	nC		
Gate-Drain Charge	Q_{gd}	_	11.9	_			
Turn-On Delay Time	t _{D(ON)}	_	39	_	ns		
Turn-On Rise Time	t _R	_	29	_	ns	$V_{GS} = 10V, V_{DS} = 325V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	122	_	ns	$R_g = 25\Omega, I_D = 8A$	
Turn-Off Fall Time	t _F		28	_	ns		
Body Diode Reverse Recovery Time	t _{RR}		570	_	ns	$dI/dt = 100A/\mu s$, $V_{DS} = 100V$,	
Body Diode Reverse Recovery Charge	Q_{RR}	_	4.17	_	μC	I _F = 8A	

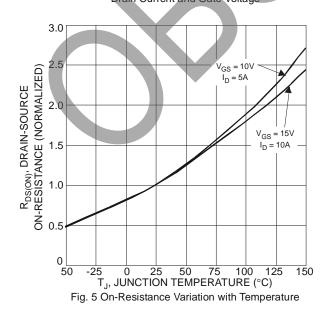
Notes:

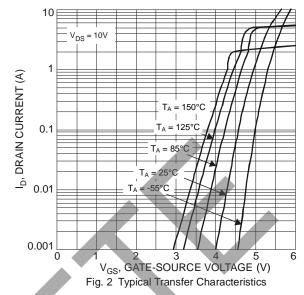
- 5. Device mounted on an infinite heatsink.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.











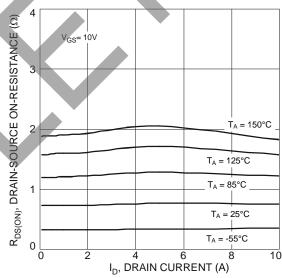


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

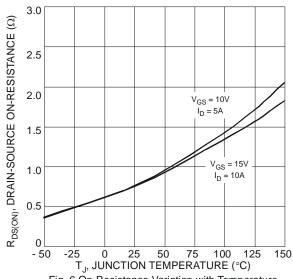


Fig. 6 On-Resistance Variation with Temperature



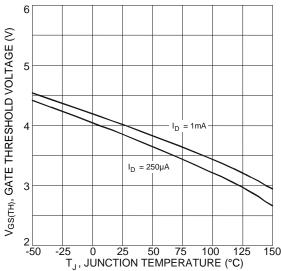
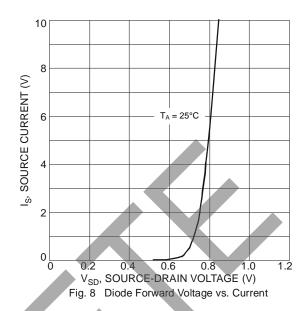
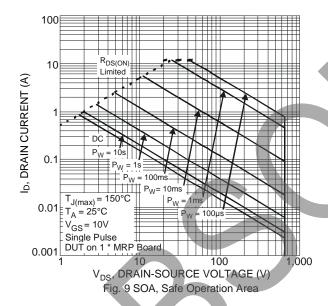
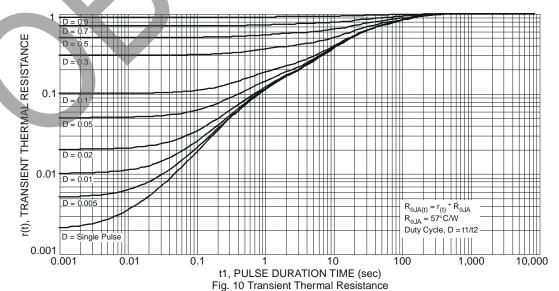


Fig. 7 Gate Threshold Variation vs. Junction Temperature





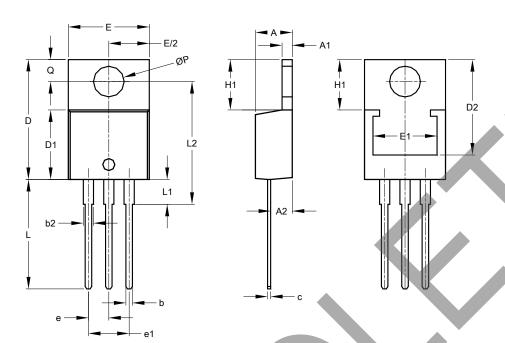




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB



TO220AB							
Dim	Min	Max	Тур				
Α	3.56	4.82	-				
A1	0.51	1.39	-				
A2	2.04	2.92	1				
b	0.39	1.01	0.81				
b2	1.15	1.77	1.24				
O	0.356	0.61	1				
ם	14.22	16.51	-				
D1	8.39	9.01	4				
D2	11.45	12.87					
е	-	1	2.54				
e1	-	-	5.08				
E	9.66	10.66	-				
E1	6.86	8.89	-				
Ħ	5.85	6.85	-				
٦	12.70	14.73	-				
L1	-	4.42	-				
L2	15.80	17.51	16.00				
Р	3.54	4.08	-				
ø	2.54	3.42	-				
All Dimensions in mm							

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance.





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